

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L13	321	L4 and ((plural\$3 or multiple) with (insulat\$3 or dielectric) with layer) and (TFT or (thin film transistor))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:40
L12	233	L11 and ((organic with (semiconductor or channel)) and ((resin or epoxy or flexible) with substrate))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:38
L11	2339	L10 and (tft or (thin film transistor))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:38
L10	5004	L9 and @ad<"20030712"	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:38
L9	10807	(438/149,151,157,161 or 257/40,57,384).cls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:38
L8	61	L7 and (coplanar with (tft or transistor))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37
L7	925	L5 and ((dielectric or insulating) with layer with substrate with gate)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37

L6	925	L5 and ((dielectric or insulating) with layer with substrate with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37
L5	2339	L4 and (tft or (thin film transistor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37
L4	5004	L3 and @ad< "20030712"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37
L3	10807	(438/149,151,157,161 or 257/40,57,384).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/14 16:37

EAST Search History (Interference)

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10/14/2009 4:40:43 PM

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